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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	792
Total RAM Bits	-
Number of I/O	120
Number of Gates	30000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	201-VFBGA, CSBGA
Supplier Device Package	201-CSP (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/aglp030v5-cs201i

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Security

Nonvolatile, flash-based IGLOO PLUS devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. IGLOO PLUS devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

IGLOO PLUS devices (except AGLP030) utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of security in the FPGA industry for programmed intellectual property and configuration data. In addition, all FlashROM data in IGLOO PLUS devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. AES was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. IGLOO PLUS devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. IGLOO PLUS devices with AES-based security provide a high level of protection for secure, remote field updates over public networks such as the Internet, and ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of the IGLOO PLUS family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. The IGLOO PLUS family, with FlashLock and AES security, is unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. An IGLOO PLUS device provides the best available security for programmable logic designs.

Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based IGLOO PLUS FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

The IGLOO PLUS devices can be operated with a 1.2 V or 1.5 V single-voltage supply for core and I/Os, eliminating the need for additional supplies while minimizing total power consumption.

Instant On

Flash-based IGLOO PLUS devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based IGLOO PLUS devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs. In addition, glitches and brownouts in system power will not corrupt the IGLOO PLUS device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based IGLOO PLUS devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

IGLOO PLUS flash FPGAs allow the user to quickly enter and exit Flash*Freeze mode. This is done almost instantly (within 1 μ s), and the device retains configuration and data in registers and RAM. Unlike SRAM-based FPGAs, the device does not need to reload configuration and design state from external memory components; instead, it retains all necessary information to resume operation immediately.

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, flash-based IGLOO PLUS devices allow all functionality to be Instant On; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and field upgrades with confidence that valuable intellectual property cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm.

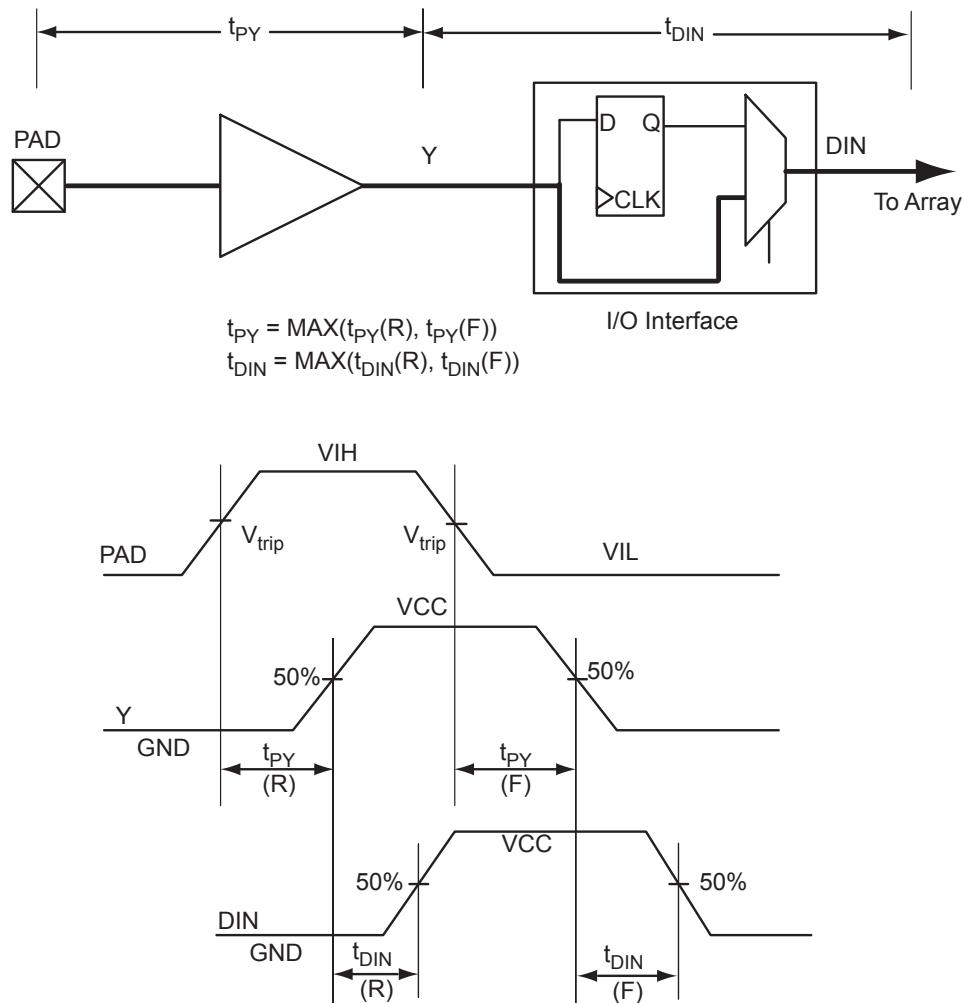


Figure 2-4 • Input Buffer Timing Model and Delays (example)

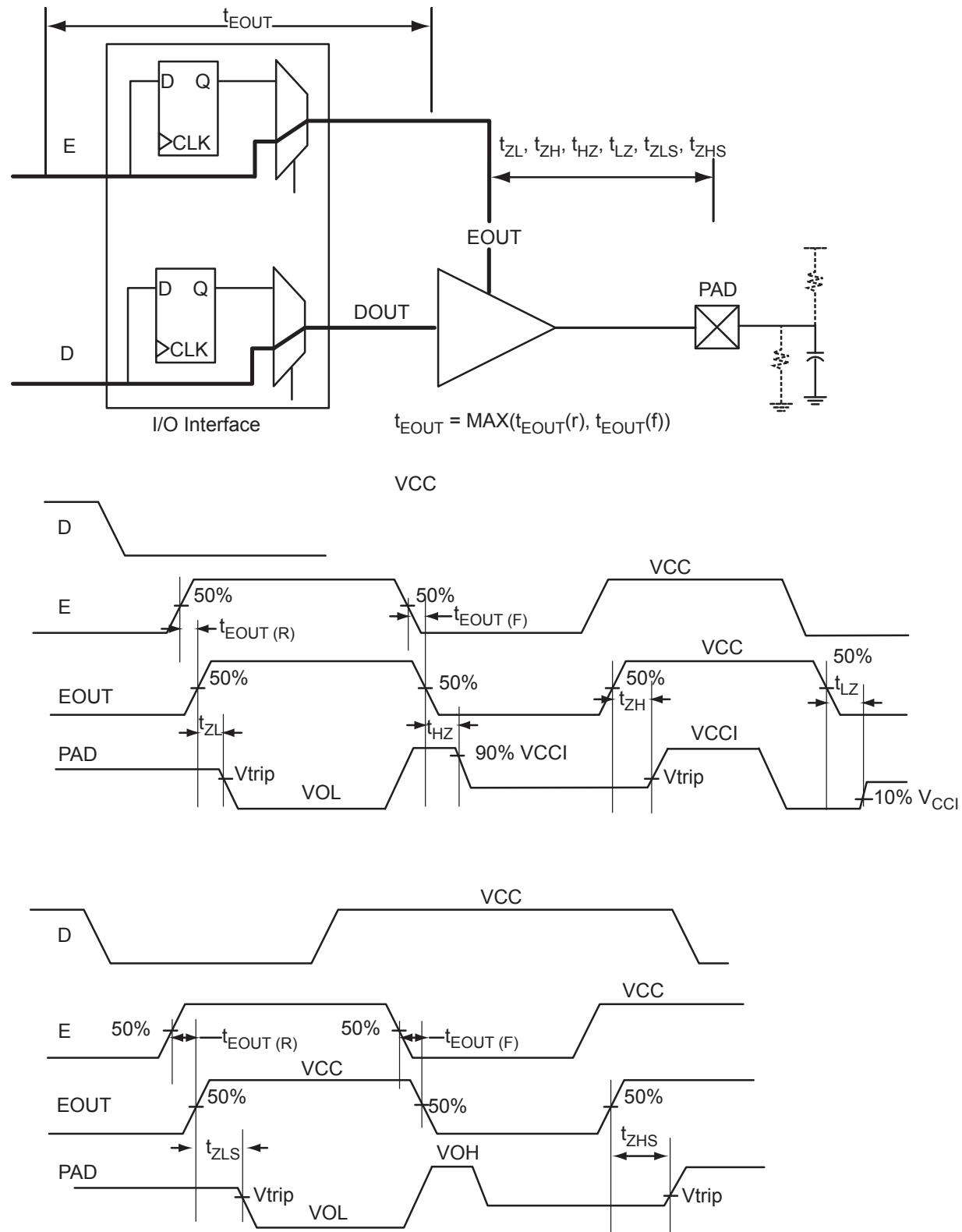


Figure 2-6 • Tristate Output Buffer Timing Model and Delays (example)

Detailed I/O DC Characteristics

Table 2-27 • Input Capacitance

Symbol	Definition	Conditions	Min.	Max.	Units
C_{IN}	Input capacitance	$V_{IN} = 0, f = 1.0 \text{ MHz}$		8	pF
C_{INCLK}	Input capacitance on the clock pin	$V_{IN} = 0, f = 1.0 \text{ MHz}$		8	pF

Table 2-28 • I/O Output Buffer Maximum Resistances¹

Standard	Drive Strength	$R_{PULL-DOWN} (\Omega)$ ²	$R_{PULL-UP} (\Omega)$ ³
3.3 V LVTTL / 3.3V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	25	75
3.3 V LVCMOS Wide Range	100 μA	Same as equivalent software default drive	
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
1.2 V LVCMOS	2 mA	157.5	163.8
1.2 V LVCMOS Wide Range ⁴	100 μA	157.5	163.8

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on V_{CC_I} , drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS model on the Microsemi SoC Products Group website at <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2. $R_{(PULL-DOWN-MAX)} = (V_{OLspec}) / I_{OLspec}$
3. $R_{(PULL-UP-MAX)} = (V_{CC_Imax} - V_{OHspec}) / I_{OHspec}$
4. Applicable to IGLOO PLUS V2 devices operating at $V_{CC_I} \geq V_{CC}$.

Single-Ended I/O Characteristics

3.3 V LVTTL / 3.3 V LVC MOS

Low-Voltage Transistor–Transistor Logic (LVTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTL input buffer and push-pull output buffer.

Table 2-34 • Minimum and Maximum DC Input and Output Levels

3.3 V LVTTL / 3.3 V LVC MOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	µA ⁴	µA ⁴
2 mA	-0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	-0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	-0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	-0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10
12 mA	-0.3	0.8	2	3.6	0.4	2.4	12	12	103	109	10	10
16 mA	-0.3	0.8	2	3.6	0.4	2.4	16	16	103	109	10	10

Notes:

1. *IIL* is the input leakage current per I/O pin over recommended operation conditions where $-0.3 \text{ V} < \text{VIN} < \text{VIL}$.
2. *IIH* is the input leakage current per I/O pin over recommended operating conditions $\text{VIH} < \text{VIN} < \text{VCCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

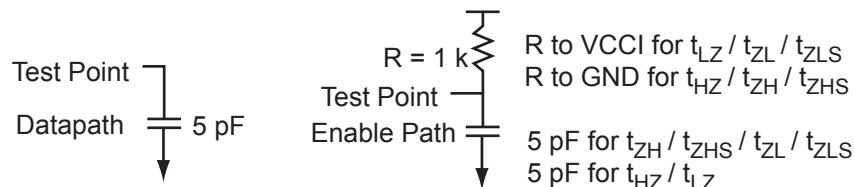


Figure 2-7 • AC Loading

Table 2-35 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	CLOAD (pF)
0	3.3	1.4	5

Note: *Measuring point = Vtrip . See [Table 2-23 on page 2-20](#) for a complete table of trip points.

Table 2-39 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	2.92	0.19	0.99	1.37	0.67	2.97	2.38	2.25	2.70	ns
4 mA	STD	0.98	2.92	0.19	0.99	1.37	0.67	2.97	2.38	2.25	2.70	ns
6 mA	STD	0.98	2.52	0.19	0.99	1.37	0.67	2.56	2.03	2.49	3.11	ns
8 mA	STD	0.98	2.52	0.19	0.99	1.37	0.67	2.56	2.03	2.49	3.11	ns
12 mA	STD	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns
16 mA	STD	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
2. Software default selection highlighted in gray

3.3 V LVCMOS Wide Range

Table 2-40 • Minimum and Maximum DC Input and Output Levels

3.3 V LVCMOS Wide Range	Equivalent Software Default Drive Strength Option ¹	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	µA	µA	Max. µA ⁴	Max. µA ⁴	µA ⁵	µA ⁵
100 µA	2 mA	-0.3	0.8	2	3.6	0.2	VDD - 0.2	100	100	25	27	10	10
100 µA	4 mA	-0.3	0.8	2	3.6	0.4	VDD - 0.2	100	100	25	27	10	10
100 µA	6 mA	-0.3	0.8	2	3.6	0.4	VDD - 0.2	100	100	51	54	10	10
100 µA	8 mA	-0.3	0.8	2	3.6	0.4	VDD - 0.2	100	100	51	54	10	10
100 µA	12 mA	-0.3	0.8	2	3.6	0.4	VDD - 0.2	100	100	103	109	10	10
100 µA	16 mA	-0.3	0.8	2	3.6	0.4	VDD - 0.2	100	100	103	109	10	10

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3 \text{ V} < \text{VIN} < \text{VIL}$.
3. IIH is the input leakage current per I/O pin over recommended operating conditions $\text{VIH} < \text{VIN} < \text{VCCI}$. Input current is larger when operating outside recommended ranges.
4. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
5. Currents are measured at 85°C junction temperature.
6. Software default selection highlighted in gray.

Table 2-41 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	3.3	1.4	5

Note: *Measuring point = V_{trip} . See [Table 2-23 on page 2-20](#) for a complete table of trip points.

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-48 • 2.5 V LVC MOS Low Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $VCC = 1.425 \text{ V}$, Worst-Case $VCCI = 2.3 \text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.97	4.44	0.18	1.06	1.22	0.66	4.53	4.15	1.80	1.70	ns
6 mA	STD	0.97	3.61	0.18	1.06	1.22	0.66	3.69	3.50	2.05	2.18	ns
8 mA	STD	0.97	3.61	0.18	1.06	1.22	0.66	3.69	3.50	2.05	2.18	ns
12 mA	STD	0.97	3.07	0.18	1.06	1.22	0.66	3.14	3.03	2.22	2.48	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-49 • 2.5 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $VCC = 1.425 \text{ V}$, Worst-Case $VCCI = 2.3 \text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.97	2.41	0.18	1.06	1.22	0.66	2.47	2.22	1.79	1.77	ns
6 mA	STD	0.97	1.99	0.18	1.06	1.22	0.66	2.04	1.75	2.04	2.25	ns
8 mA	STD	0.97	1.99	0.18	1.06	1.22	0.66	2.04	1.75	2.04	2.25	ns
12 mA	STD	0.97	1.77	0.18	1.06	1.22	0.66	1.81	1.51	2.22	2.56	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
2. Software default selection highlighted in gray.

Applies to 1.2 V DC Core Voltage

Table 2-50 • 2.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $VCC = 1.14 \text{ V}$, Worst-Case $VCCI = 2.3 \text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.98	5.04	0.19	1.19	1.40	0.67	5.12	4.65	2.22	2.36	ns
6 mA	STD	0.98	4.19	0.19	1.19	1.40	0.67	4.25	3.98	2.48	2.85	ns
8 mA	STD	0.98	4.19	0.19	1.19	1.40	0.67	4.25	3.98	2.48	2.85	ns
12 mA	STD	0.98	3.63	0.19	1.19	1.40	0.67	3.69	3.50	2.66	3.16	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-51 • 2.5 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $VCC = 1.14 \text{ V}$, Worst-Case $VCCI = 2.3 \text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
4 mA	STD	0.98	2.96	0.19	1.19	1.40	0.67	3.00	2.67	2.22	2.46	ns
6 mA	STD	0.98	2.52	0.19	1.19	1.40	0.67	2.56	2.18	2.47	2.95	ns
8 mA	STD	0.98	2.52	0.19	1.19	1.40	0.67	2.56	2.18	2.47	2.95	ns
12 mA	STD	0.98	2.29	0.19	1.19	1.40	0.67	2.32	1.94	2.65	3.27	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
2. Software default selection highlighted in gray.

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-52 • Minimum and Maximum DC Input and Output Levels

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min., V	Max., V	Min., V	Max., V	Max., V	Min., V	mA	mA	Max., mA ³	Max., mA ³	μA ⁴	μA ⁴
2 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI - 0.45	2	2	9	11	10	10
4 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI - 0.45	4	4	17	22	10	10
6 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI - 0.45	6	6	35	44	10	10
8 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI - 0.45	8	8	35	44	10	10

Notes:

1. *IIL* is the input leakage current per I/O pin over recommended operation conditions where $-0.3 \text{ V} < \text{VIN} < \text{VIL}$.
2. *IIH* is the input leakage current per I/O pin over recommended operating conditions $\text{VIH} < \text{VIN} < \text{VCCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

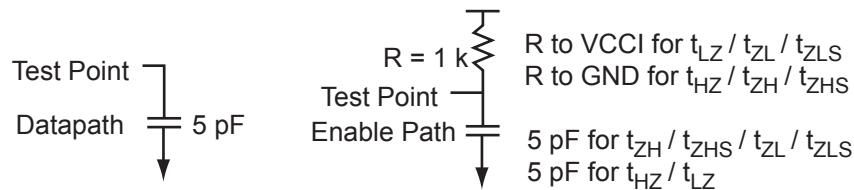


Figure 2-9 • AC Loading

Table 2-53 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.8	0.9	5

Note: *Measuring point = V_{trip} . See [Table 2-23 on page 2-20](#) for a complete table of trip points.

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-60 • 1.5 V LVC MOS Low Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425 \text{ V}$, Worst-Case $V_{CCI} = 1.4 \text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	6.07	0.18	1.16	1.62	0.66	6.19	5.53	2.13	2.02	ns
4 mA	STD	0.97	5.24	0.18	1.16	1.62	0.66	5.34	4.81	2.37	2.47	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-61 • 1.5 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425 \text{ V}$, Worst-Case $V_{CCI} = 1.4 \text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	2.65	0.18	1.16	1.62	0.66	2.71	2.43	2.13	2.11	ns
4 mA	STD	0.97	2.29	0.18	1.16	1.62	0.66	2.33	2.00	2.37	2.57	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
2. Software default selection highlighted in gray.

Applies to 1.2 V DC Core Voltage

Table 2-62 • 1.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14 \text{ V}$, Worst-Case $V_{CCI} = 1.4 \text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	6.57	0.19	1.26	1.80	0.67	6.68	6.01	2.54	2.59	ns
4 mA	STD	0.98	5.72	0.19	1.26	1.80	0.67	5.81	5.27	2.79	3.05	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-63 • 1.5 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14 \text{ V}$, Worst-Case $V_{CCI} = 1.4 \text{ V}$

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	3.08	0.19	1.26	1.80	0.67	3.13	2.82	2.53	2.68	ns
4 mA	STD	0.98	2.71	0.19	1.26	1.80	0.67	2.75	2.39	2.78	3.15	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
2. Software default selection highlighted in gray.

Input Register

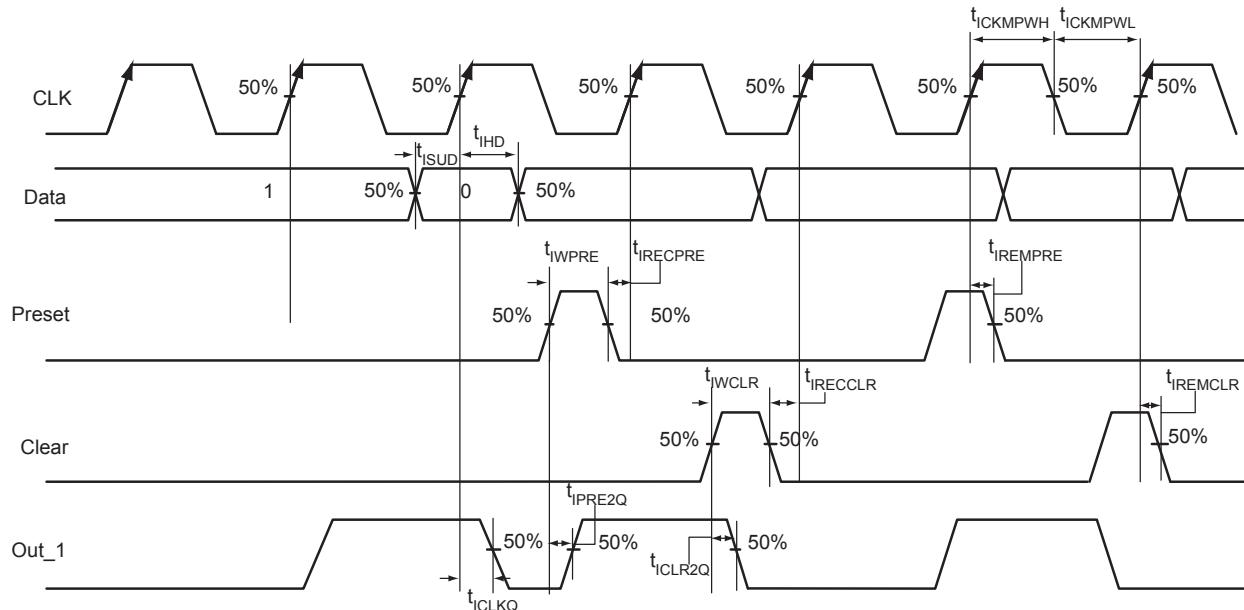


Figure 2-14 • Input Register Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-74 • Input Data Register Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425 \text{ V}$

Parameter	Description	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.41	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.32	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.57	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.57	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t_{IPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width High for the Input Data Register	0.31	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width Low for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage
Table 2-75 • Input Data Register Propagation Delays

 Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14 \text{ V}$

Parameter	Description	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.66	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.43	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.86	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.86	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width High for the Input Data Register	0.31	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width Low for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

1.2 V DC Core Voltage
Table 2-79 • Output Enable Register Propagation Delays

 Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14 \text{ V}$

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	1.06	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.52	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	1.25	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	1.36	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{OERECCR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-6](#) for derating values.

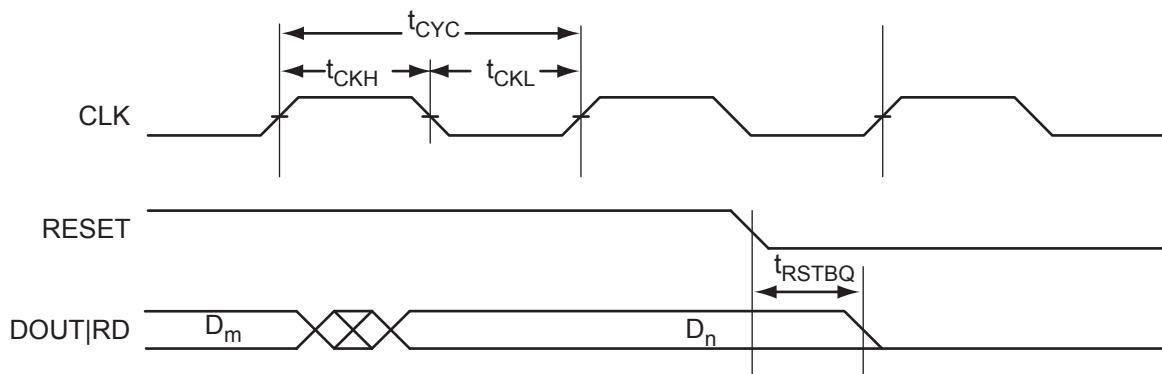


Figure 2-28 • RAM Reset

Table 2-93 • RAM512X18Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.69	ns
t_{AH}	Address hold time	0.13	ns
t_{ENS}	REN, WEN setup time	0.61	ns
t_{ENH}	REN, WEN hold time	0.07	ns
t_{DS}	Input data (WD) setup time	0.59	ns
t_{DH}	Input data (WD) hold time	0.30	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	3.51	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	1.43	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.21	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.25	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	1.72	ns
	RESET Low to data out Low on RD (pipelined)	1.72	ns
$t_{REMRSTB}$	RESET removal	0.51	ns
$t_{RECRSTB}$	RESET recovery	2.68	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

3 – Pin Descriptions and Packaging

Supply Pins

GND**Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ**Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC**Core Supply Voltage**

Supply voltage to the FPGA core, nominally 1.5 V for IGLOO PLUS V5 devices, and 1.2 V or 1.5 V for IGLOO PLUS V2 devices. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

For IGLOO PLUS V2 devices, VCC can be switched dynamically from 1.2 V to 1.5 V or vice versa. This allows in-system programming (ISP) when VCC is at 1.5 V and the benefit of low power operation when VCC is at 1.2 V.

VCCI_{Bx}**I/O Supply Voltage**

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are four I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCI_{Bx} supply. VCCI can be 1.2 V, 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VCCI pins tied to GND.

VMV_x**I/O Supply Voltage (quiet)**

Quiet supply voltage to the input buffers of each I/O bank. x is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMV_x supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMV_x can be 1.2 V, 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCI_{B0}, VMV1 to VCCI_{B1}, etc.).

VCCPLA/B/C/D/E/F**PLL Supply Voltage**

Supply voltage to analog PLL, nominally 1.5 V or 1.2 V, depending on the device.

- 1.5 V for IGLOO PLUS V5 devices
- 1.2 V or 1.5 V for IGLOO PLUS V2 devices

When the PLLs are not used, the Microsemi Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed signal FPGAs" chapter of the [IGLOO PLUS FPGA Fabric User's Guide](#) for a complete board solution for the PLL analog power supply and ground.

There is one VCCPLF pin on IGLOO PLUS devices.

JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

TCK

Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 kΩ will satisfy the requirements. Refer to [Table 3-2](#) for more information.

Table 3-2 • Recommended Tie-Off Values for the TCK and TRST Pins

VJTAG	Tie-Off Resistance
VJTAG at 3.3 V	200 Ω to 1 kΩ
VJTAG at 2.5 V	200 Ω to 1 kΩ
VJTAG at 1.8 V	500 Ω to 1 kΩ
VJTAG at 1.5 V	500 Ω to 1 kΩ

Notes:

1. *Equivalent parallel resistance if more than one device is on the JTAG chain*
2. *The TCK pin can be pulled up/down.*
3. *The TRST pin is pulled down.*

TDI

Test Data Input

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO

Test Data Output

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

TMS

Test Mode Select

The TMS pin controls the use of the IEEE 1532 boundary scan pins (TCK, TDI, TDO, TRST). There is an internal weak pull-up resistor on the TMS pin.

TRST

Boundary Scan Reset Pin

The TRST pin functions as an active-low input to asynchronously initialize (or reset) the boundary scan circuitry. There is an internal weak pull-up resistor on the TRST pin. If JTAG is not used, an external pull-down resistor could be included to ensure the test access port (TAP) is held in reset mode. The resistor values must be chosen from [Table 3-2](#) and must satisfy the parallel resistance value requirement. The values in [Table 3-2](#) correspond to the resistor recommended when a single device is used, and the equivalent parallel resistor when multiple devices are connected via a JTAG chain.

In critical applications, an upset in the JTAG circuit could allow entrance to an undesired JTAG state. In such cases, Microsemi recommends tying off TRST to GND through a resistor placed close to the FPGA pin.

Note that to operate at all VJTAG voltages, 500 Ω to 1 kΩ will satisfy the requirements.

VQ176	
Pin Number	AGLP060 Function
1	GAA2/IO156RSB3
2	IO155RSB3
3	GAB2/IO154RSB3
4	IO153RSB3
5	GAC2/IO152RSB3
6	GND
7	VCCIB3
8	IO149RSB3
9	IO147RSB3
10	IO145RSB3
11	IO144RSB3
12	IO143RSB3
13	VCC
14	IO141RSB3
15	GFC1/IO140RSB3
16	GFB1/IO138RSB3
17	GFB0/IO137RSB3
18	VCOMPLF
19	GFA1/IO136RSB3
20	VCCPLF
21	GFA0/IO135RSB3
22	GND
23	VCCIB3
24	GFA2/IO134RSB3
25	GFB2/IO133RSB3
26	GFC2/IO132RSB3
27	IO131RSB3
28	IO130RSB3
29	IO129RSB3
30	IO127RSB3
31	IO126RSB3
32	IO125RSB3
33	IO123RSB3
34	IO122RSB3
35	IO121RSB3

VQ176	
Pin Number	AGLP060 Function
36	IO119RSB3
37	GND
38	VCCIB3
39	GEC1/IO116RSB3
40	GEB1/IO114RSB3
41	GEC0/IO115RSB3
42	GEB0/IO113RSB3
43	GEA1/IO112RSB3
44	GEA0/IO111RSB3
45	GEA2/IO110RSB2
46	NC
47	FF/GEB2/IO109R SB2
48	GEC2/IO108RSB2
49	IO106RSB2
50	IO107RSB2
51	IO104RSB2
52	IO105RSB2
53	IO102RSB2
54	IO103RSB2
55	GND
56	VCCIB2
57	IO101RSB2
58	IO100RSB2
59	IO99RSB2
60	IO98RSB2
61	IO97RSB2
62	IO96RSB2
63	IO95RSB2
64	IO94RSB2
65	IO93RSB2
66	VCC
67	IO92RSB2
68	IO91RSB2
69	IO90RSB2

VQ176	
Pin Number	AGLP060 Function
70	IO89RSB2
71	IO88RSB2
72	IO87RSB2
73	IO86RSB2
74	IO85RSB2
75	IO84RSB2
76	GND
77	VCCIB2
78	IO83RSB2
79	IO82RSB2
80	GDC2/IO80RSB2
81	IO81RSB2
82	GDA2/IO78RSB2
83	GDB2/IO79RSB2
84	NC
85	NC
86	TCK
87	TDI
88	TMS
89	VPUMP
90	TDO
91	TRST
92	VJTAG
93	GDA1/IO76RSB1
94	GDC0/IO73RSB1
95	GDB1/IO74RSB1
96	GDC1/IO72RSB1
97	VCCIB1
98	GND
99	IO70RSB1
100	IO69RSB1
101	IO67RSB1
102	IO66RSB1
103	IO65RSB1
104	IO63RSB1

CS201	
Pin Number	AGLP060 Function
H14	IO64RSB1
H15	IO62RSB1
J1	GFA2/IO134RSB3
J2	GFA0/IO135RSB3
J3	GFB2/IO133RSB3
J4	IO131RSB3
J6	VCCIB3
J7	GND
J8	VCC
J9	GND
J10	VCCIB1
J12	IO61RSB1
J13	IO63RSB1
J14	IO68RSB1
J15	IO66RSB1
K1	IO130RSB3
K2	GFC2/IO132RSB3
K3	IO127RSB3
K4	IO129RSB3
K6	GND
K7	VCCIB2
K8	VCCIB2
K9	VCCIB2
K10	VCCIB1
K12	IO65RSB1
K13	IO67RSB1
K14	IO69RSB1
K15	IO70RSB1
L1	IO126RSB3
L2	IO128RSB3
L3	IO121RSB3
L4	IO123RSB3
L12	GDB1/IO74RSB1
L13	GDC1/IO72RSB1
L14	IO71RSB1

CS201	
Pin Number	AGLP060 Function
L15	GDC0/IO73RSB1
M1	IO122RSB3
M2	IO124RSB3
M3	IO119RSB3
M4	GND
M5	IO125RSB3
M6	IO98RSB2
M7	IO96RSB2
M8	IO91RSB2
M9	IO89RSB2
M10	IO82RSB2
M11	GDA2/IO78RSB2
M12	GND
M13	GDA1/IO76RSB1
M14	GDA0/IO77RSB1
M15	GDB0/IO75RSB1
N1	IO117RSB3
N2	IO120RSB3
N3	GND
N4	GEB1/IO114RSB3
N5	IO107RSB2
N6	IO100RSB2
N7	IO94RSB2
N8	IO87RSB2
N9	IO85RSB2
N10	GDC2/IO80RSB2
N11	IO90RSB2
N12	IO84RSB2
N13	GND
N14	TDO
N15	VJTAG
P1	GEC0/IO115RSB3
P2	GEC1/IO116RSB3
P3	GEA0/IO111RSB3
P4	GEA1/IO112RSB3

CS201	
Pin Number	AGLP060 Function
P5	IO106RSB2
P6	IO105RSB2
P7	IO103RSB2
P8	IO99RSB2
P9	IO93RSB2
P10	IO92RSB2
P11	IO95RSB2
P12	IO86RSB2
P13	IO83RSB2
P14	VPUMP
P15	TRST
R1	IO118RSB3
R2	GEB0/IO113RSB3
R3	GEA2/IO110RSB2
R4	FF/GEB2/IO109RS B2
R5	GEC2/IO108RSB2
R6	IO102RSB2
R7	IO101RSB2
R8	IO104RSB2
R9	IO97RSB2
R10	IO88RSB2
R11	IO81RSB2
R12	GDB2/IO79RSB2
R13	TMS
R14	TDI
R15	TCK

CS281	
Pin Number	AGLP125 Function
H8	VCC
H9	VCCIB0
H10	VCC
H11	VCCIB0
H12	VCC
H13	VCCIB1
H15	IO77RSB1
H16	GCB0/IO82RSB1
H18	GCA1/IO83RSB1
H19	GCA2/IO85RSB1
J1	VCOMPLF
J2	GFA0/IO189RSB3
J4	VCCPLF
J5	GFC0/IO193RSB3
J7	GFA2/IO188RSB3
J8	VCCIB3
J9	GND
J10	GND
J11	GND
J12	VCCIB1
J13	GCC1/IO79RSB1
J15	GCA0/IO84RSB1
J16	GCB2/IO86RSB1
J18	IO76RSB1
J19	IO78RSB1
K1	VCCIB3
K2	GFA1/IO190RSB3
K4	GND
K5	IO19RSB0
K7	IO197RSB3
K8	VCC
K9	GND
K10	GND
K11	GND
K12	VCC
K13	GCC2/IO87RSB1

CS281	
Pin Number	AGLP125 Function
K15	IO89RSB1
K16	GND
K18	IO88RSB1
K19	VCCIB1
L1	GFB2/IO187RSB3
L2	IO185RSB3
L4	GFC2/IO186RSB3
L5	IO184RSB3
L7	IO199RSB3
L8	VCCIB3
L9	GND
L10	GND
L11	GND
L12	VCCIB1
L13	IO95RSB1
L15	IO91RSB1
L16	NC
L18	IO90RSB1
L19	NC
M1	IO180RSB3
M2	IO179RSB3
M4	IO181RSB3
M5	IO183RSB3
M7	VCCIB3
M8	VCC
M9	VCCIB2
M10	VCC
M11	VCCIB2
M12	VCC
M13	VCCIB1
M15	IO122RSB2
M16	IO93RSB1
M18	IO92RSB1
M19	NC
N1	IO178RSB3
N2	IO175RSB3

CS281	
Pin Number	AGLP125 Function
N4	IO182RSB3
N5	IO161RSB2
N7	GEA2/IO164RSB2
N8	VCCIB2
N9	IO137RSB2
N10	IO135RSB2
N11	IO131RSB2
N12	VCCIB2
N13	VPUMP
N15	IO117RSB2
N16	IO96RSB1
N18	IO98RSB1
N19	IO94RSB1
P1	IO174RSB3
P2	GND
P3	IO176RSB3
P4	IO177RSB3
P5	GEA0/IO165RSB3
P15	IO111RSB2
P16	IO108RSB2
P17	GDC1/IO99RSB1
P18	GND
P19	IO97RSB1
R1	IO173RSB3
R2	IO172RSB3
R4	GEC1/IO170RSB3
R5	GEB1/IO168RSB3
R6	IO154RSB2
R7	IO149RSB2
R8	IO146RSB2
R9	IO138RSB2
R10	IO134RSB2
R11	IO132RSB2
R12	IO130RSB2
R13	IO118RSB2
R14	IO112RSB2